

Probing magnetic anisotropies in half-metallic CrO₂ epitaxial films by FMR

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Abstract

Epitaxial (100) thin films of CrO₂ were fabricated by chemical vapour deposition technique onto TiO₂ (100) single-crystal substrates. X-band (9.5 GHz) ferromagnetic resonance studies reveal that magnetic anisotropy parameters in the series prepared using CrO₂Cl₂ liquid precursor show only slight variations with thickness, contrary to their strong dependence observed in the CrO₃-based films. The different behaviour was attributed to different morphologies of the films prepared using solid and liquid precursors.

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1. Introduction

The highly spin-polarized conduction band of half-metallic ferromagnets makes them ideal candidates for spintronic applications. The half-metallic chromium dioxide (CrO₂) has the highest polarization (~100%) [1–5]. Epitaxial CrO₂ films have been synthesized by chemical vapour deposition (CVD) technique [6], and there are few papers on their electrical and magnetic properties [3–10]. Recently, it has been shown that CVD process with a liquid precursor [11] is more advantageous in terms of quality of the films than the solid precursor used previously.

In this work the CrO₂ epitaxial thin films, fabricated by the CrO₂Cl₂ liquid precursor CVD process, were studied by the ferromagnetic resonance (FMR) technique. The magnetic anisotropies of the films have been probed, and compared with the results reported previously [12].

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2. Experimental

Epitaxial (100) thin films of CrO₂ were fabricated by chemical vapour deposition (CVD) technique with use of the CrO₂Cl₂ liquid precursor onto TiO₂ (100) single-crystal substrates, as described elsewhere [11]. The film thickness ranged from 350 Å to 1350 Å. *Digital Instruments NanoScope IV* scanning probe microscope was used to study the surface morphology of the films. Ferromagnetic resonance (FMR) studies were performed at the X-band (9.5 GHz) Bruker EMX spectrometer at room temperature.

3. Results and discussion

The surface images of the CrO₂ films with a thickness of 350 and 1350 Å obtained in the contact mode are shown in Fig. 1. The individual CrO₂ grains, growing epitaxially on the TiO₂ substrate, forms fairly regular rectangular-shaped blocks with the lateral size of about 150 nm. The roughness of the films decreases drastically for the thicker films, and the grain structure is not clearly observable in AFM scans of the thicker films.

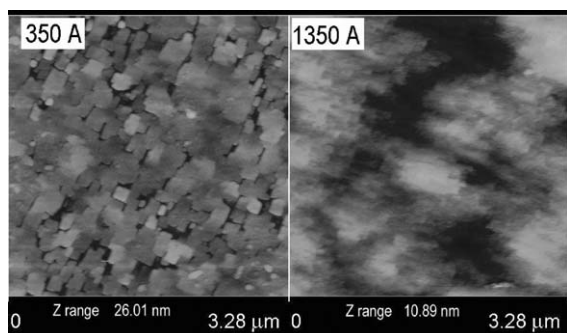


Fig. 1. Height-mode AFM scans of the CrO₂ film with the thickness of 350 Å (left) and 1350 Å (right).

FMR measurements in both “in-plane” and “out-of-plane” geometries of the films with respect to an external DC magnetic field were performed. Highly anisotropic FMR signal was observed, which demonstrates splitting into the surface, bulk, spin-wave and magnetostatic modes (Fig. 2). For instance, the two FMR lines observed along the easy axis direction are the bulk and surface modes.

The dependence of the FMR spectra on orientation was similar to that observed previously in the series of films grown from the CrO₃ solid precursor [12]. The out-of-plane angular dependence exhibits dominant contribution of the shape anisotropy, while the in-plane measurements reveal the essential in-plane magnetocrystalline anisotropy. For all CrO₂ film thicknesses the easy axis of the magnetization at room temperature is aligned along the crystallographic *c* direction of the single-crystalline films, that agrees with our earlier results for the solid precursor series [12]. It is remarkable that the FMR spectra show very small variation with thickness (Fig. 2). This indicates that the magnetic anisotropy parameters in the CrO₂Cl₂-grown films does not depend on the thickness, contrary to that of the CrO₃-based films, where strong dependence on the thickness was observed [12]. Values of *g*-factor, effective magnetization and the in-plane anisotropy field were estimated to be about of 1.98, 530 and 700 G, respectively. Furthermore, these parameters are very close to the values for the *thicker* films of CrO₃-based series [12]. We attribute the different behaviour of the magnetic anisotropies as a function of thickness to various morphologies of the films prepared using solid and liquid precursors. It is known that the lattice mismatch produces the magnetoelastic anisotropy in the plane of the CrO₂ film [6]. Obviously, the stress due to the lattice mismatch with the substrate is greatly reduced as a result of the plaquet growth (Fig. 1). Besides, the multiple magnetostatic modes observed in FMR spectra (right panel in Fig. 2) indicate exchange decoupling at plaquet boundaries as well. Therefore, the breaks in the nearest to the substrate layer of the epitaxial CrO₂ film are apparently relevant for relaxation of the tensile stress due to the lattice

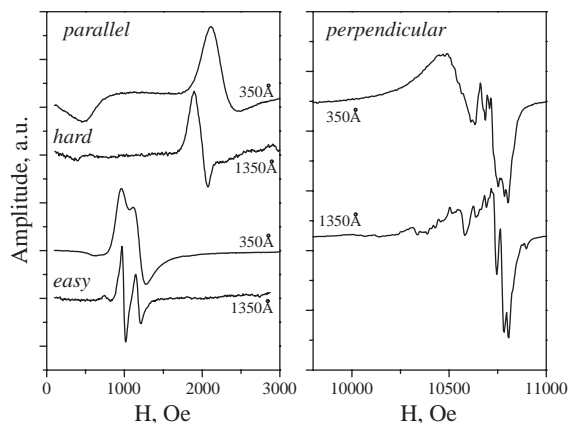


Fig. 2. FMR spectra of CrO₂ films with the thickness of 350 and 1350 Å for perpendicular (right) and parallel (left) orientations of DC magnetic field with respect to the film plane. The easy and hard axis directions are also labelled.

mismatch, greatly decreasing the magnetoelastic anisotropy in the CrO₂Cl₂ liquid-precursor films.

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